Abstracts

Techniques for Improving the Stability and Amplifier Performance of X-Band GaAs Power FETs

S.J. Temple, Z. Galani, R.M. Healy and B.S. Hewitt. "Techniques for Improving the Stability and Amplifier Performance of X-Band GaAs Power FETs." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 390-392.

Via hole source connections together with on-carrier matching significantly improve X-band power FET performance. Via hole connections eliminate spurious oscillations by reducing common-lead source inductance. On-carrier matching networks improve the power and gain of X-band FET amplifiers by partially matching the very low input and output impedance of large periphery devices with impedance transformation networks located as close to the transistor as possible.

❑ Return to main document.